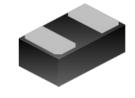


# **Bi-directional 7V High Capacitance ESD Protector**

#### **Description**

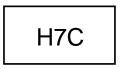
The PESDHC2FD7VB protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.



DFN1006-2L(Bottom View)

#### **Feature**

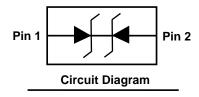
- $\rightarrow$  300W peak pulse power per line ( $t_P = 8/20\mu s$ )
- DFN1006-2L package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically < 1ns</p>
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC61000-4-4 (EFT) 40A (5/50ns)



Marking (Top View)

### **Applications**

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

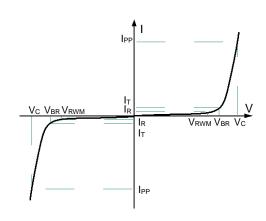


#### **Mechanical Characteristics**

- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- DFN1006-2L without plating

### **Electronics Parameter**

Symbol	Parameter		
V <sub>RWM</sub>	Peak Reverse Working Voltage		
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>		
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>		
lτ	Test Current		
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P <sub>PP</sub>	Peak Pulse Power		
CJ	Junction Capacitance		
lF	Forward Current		
VF	Forward Voltage @ I <sub>F</sub>		



## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	Vrwm				7.0	V
Breakdown Voltage	V <sub>BR</sub>	It = 1mA	7.5	9.0	10.0	V
Reverse Leakage Current	lr	Vrwм = 7V T=25°С			1.0	μA
Clamping Voltage	VcL	I <sub>PP</sub> =16A t <sub>p</sub> =100ns		11.0		V
Clamping Voltage	Vc	I <sub>PP</sub> =1A t <sub>P</sub> = 8/20µs		11.0	12.0	V
Clamping Voltage	Vc	IPP=7A tp = 8/20µs		14.0	15.0	V
Clamping Voltage	Vc	I <sub>PP</sub> =14.5A t <sub>P</sub> = 8/20μs		19.0	21.0	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz		39.0	45.0	pF

# Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t <sub>P</sub> =8/20μs)	P <sub>pp</sub>	300	W
Peak Pulse Current (t <sub>p</sub> =8/20μs)	I <sub>pp</sub>	14.5	A
Operating Temperature	Τυ	-55 to 150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C

### Typical Characteristics



Fig 1.Pulse Waveform

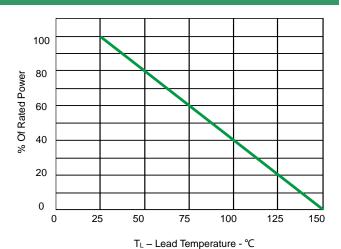


Fig 2.Power Derating Curve

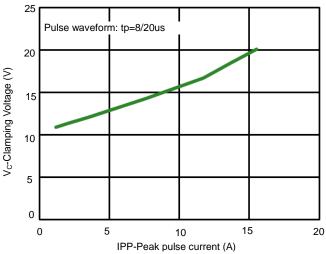


Fig 3. Clamping voltage vs. Peak pulse current

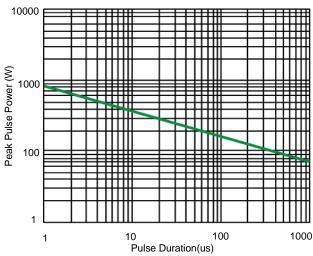


Fig 4. Non-Repetitive Peak Pulse Power vs. Pulse time

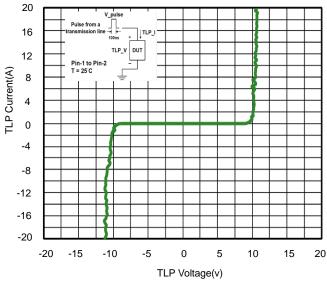


Fig 5. TLP Measurement

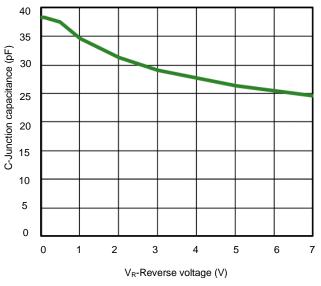
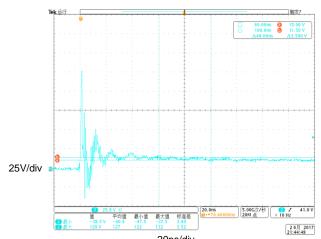
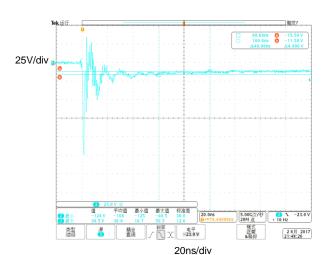


Fig 6. Capacitance vs. Reveres voltage

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20ns/div Fig 7. ESD clamping voltage (IEC61000-4-2 +8KV contact)



20ns/div Fig 8. ESD clamping voltage (IEC61000-4-2-8KV contact)

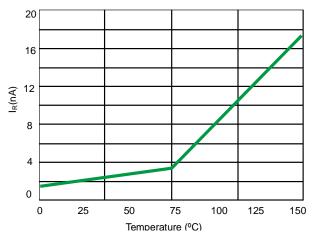
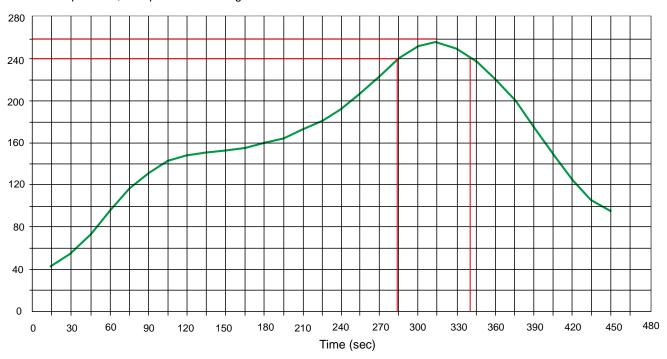


Fig 9. Typical Leakage Current vs. Temperature

#### **Solder Reflow Recommendation**

Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec

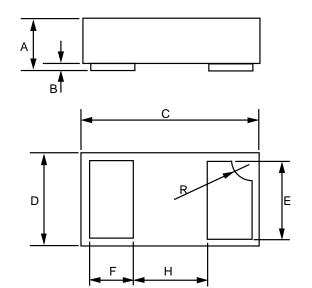


### **PCB Design**

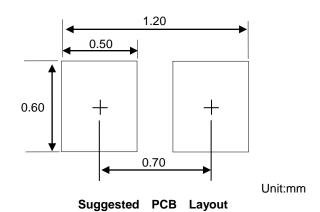
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- > Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

# Product dimension (DFN1006-2L)



Dim	Inc	hes	Millimeters		
	MIN	MAX	MIN	MAX	
Α	0.013	0.020	0.34	0.50	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Typ.		0.40	Тур.	
R	0.001	0.005	0.05	0.15	



# Ordering information

Device	Package	Reel	Shipping
PESDHC2FD7VB	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel

### Load with information





Unit: mm

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